

GENERAL DESCRIPTION

The SGM6060 is a high voltage and high frequency Buck converter with 2A maximum output current and integrated high-side power MOSFET. It implements peak current mode control to simplify external compensation design.

With a wide input voltage range of 3.8V to 55V, it is suitable for a broad range of applications such as industry equipment.

The SGM6060 operates at fixed frequency and enters PFM (Pulse Frequency Modulation) mode automatically at light loads to maintain high efficiency. During startup and thermal shutdown, the frequency foldback technique is used to avoid inductor current runaway for reliable and fault tolerant operation. The current limit foldback technique is used for reducing power consumption during output shorted and suppressing output voltage overshoot during recovery.

Switching frequency can be set as high as 2MHz. It minimizes the EMI noise issues that could interfere with nearby systems such as AM radio or ADSL modems.

The SGM6060 is available in Green TDFN-3×3-10L and SOIC-8 (Exposed Pad) packages.

FEATURES

- 3.8V to 55V Wide Input Voltage Range
- Adjustable Output Voltage
- Up to 95% Efficiency
- PFM Mode at Light Loads
- Quiescent Current: 126µA (TYP)
- Less than 18µA Shutdown Current
- Internal HS Power MOSFET $R_{DS(ON)}$: 220mΩ (TYP)
- Adjustable Switching Frequency: 200kHz to 2MHz
- Internal Soft-Start Circuit
- Accurate EN Input Threshold
- Stable with Ceramic Capacitor
- Available in Green TDFN-3×3-10L and SOIC-8 (Exposed Pad) Packages

APPLICATIONS

- Industrial and Commercial Power Systems
- Distributed Power Systems
- Aftermarket Automotive Accessories

TYPICAL APPLICATION

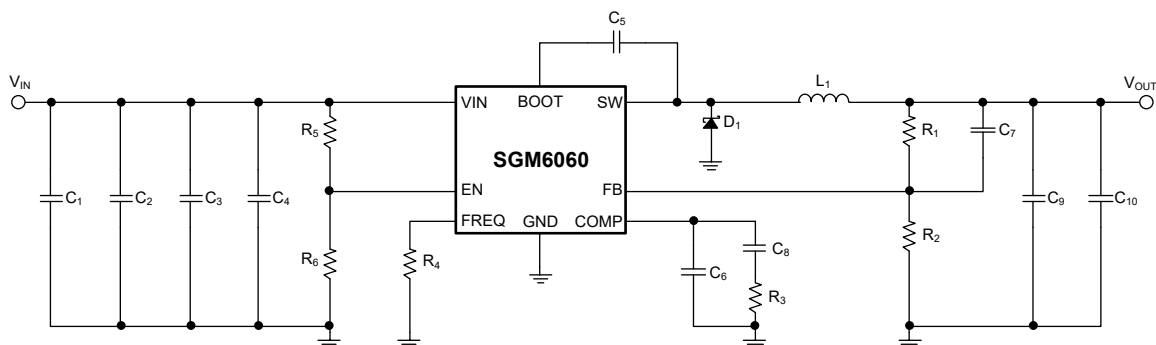


Figure 1. Typical Application Circuit

PACKAGE/ORDERING INFORMATION

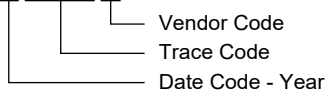
MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM6060	TDFN-3x3-10L	-40°C to +125°C	SGM6060XTD10G/TR	SGM 6060D XXXXX	Tape and Reel, 4000
	SOIC-8 (Exposed Pad)	-40°C to +125°C	SGM6060XPS8G/TR	SGM 6060XPS8 XXXXX	Tape and Reel, 4000

MARKING INFORMATION

NOTE: XXXXX = Date Code, Trace Code and Vendor Code.

TDFN-3x3-10L/SOIC-8 (Exposed Pad)

XXXXX



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

- Supply Voltage Range, V_{IN} -0.3V to 60V
- Switch Voltage Range, V_{SW} -0.5V to $V_{IN} + 0.5V$
- BOOT to SW -0.3V to 5V
- EN Pin Voltage Range, V_{EN} -0.3V to $V_{IN} + 0.3V$
- All Other Pins -0.3V to 5V
- Package Thermal Resistance
- TDFN-3x3-10L, θ_{JA} 77°C/W
- SOIC-8 (Exposed Pad), θ_{JA} 53°C/W
- unction Temperature +150°C
- Storage Temperature Range -65°C to +150°C
- Lead Temperature (Soldering, 10s) +260°C
- ESD Susceptibility
- HBM 3000V
- CDM 1000V

RECOMMENDED OPERATING CONDITIONS

- Supply Voltage Range, V_{IN} 3.8V to 55V
- Operating Junction Temperature Range -40°C to +125°C

OVERSTRESS CAUTION

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

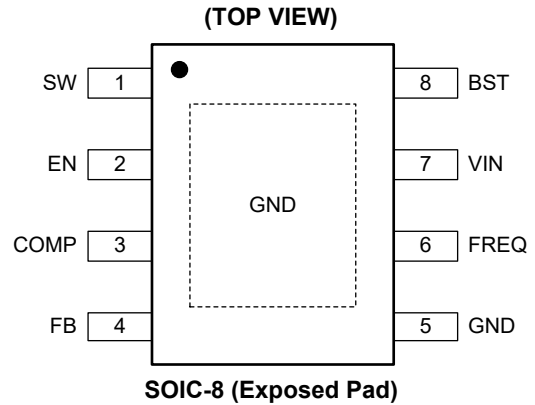
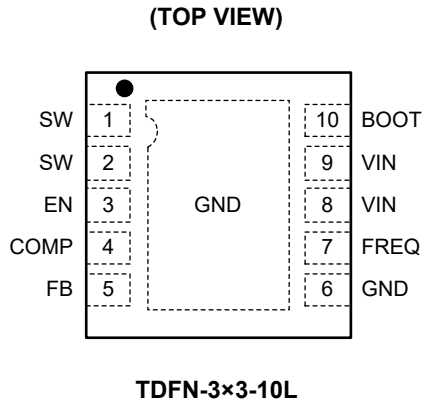
ESD SENSITIVITY CAUTION

This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

PIN CONFIGURATION



PIN DESCRIPTION

PIN		NAME	FUNCTION
TDFN-3x3-10L	SOIC-8 (Exposed Pad)		
1, 2	1	SW	Switching Node of the Converter.
3	2	EN	Active High Enable Input Pin. It has a weak internal pull-up current source. Pull it below 1.12V to disable the device. Leave EN pin floating when unused. When EN pin is directly connected to VIN pin or external signal source, a resistor greater than 10kΩ is necessary.
4	3	COMP	Transconductance Error Amplifier Output. Use a compensation network between COMP and GND pins to compensate the internal loop.
5	4	FB	Inverting Input of the Error Amplifier.
6	5	GND	Ground Pin.
7	6	FREQ	Adjustable Switching Frequency Pin. Connect an external resistor between FREQ and GND pins to adjust the switching frequency.
8, 9	7	VIN	Power Supply Input Pin.
10	8	BOOT	Power Supply of the Internal MOSFET Gate Driver. Connect a 0.1μF bootstrap capacitor between BOOT and SW pins.
—	—	Exposed Pad	Exposed Pad. It should be soldered to the ground plane for enhanced heat dissipation.

ELECTRICAL CHARACTERISTICS

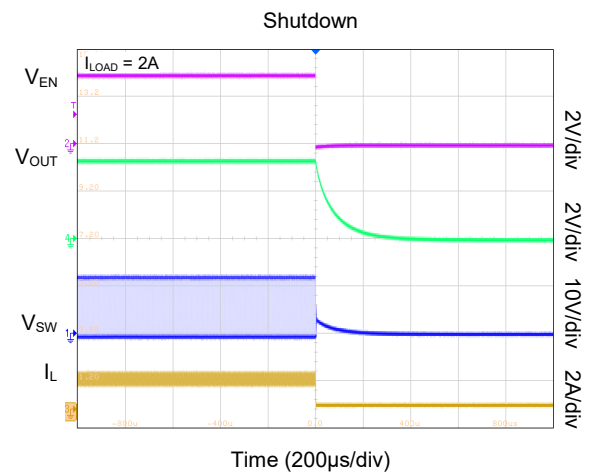
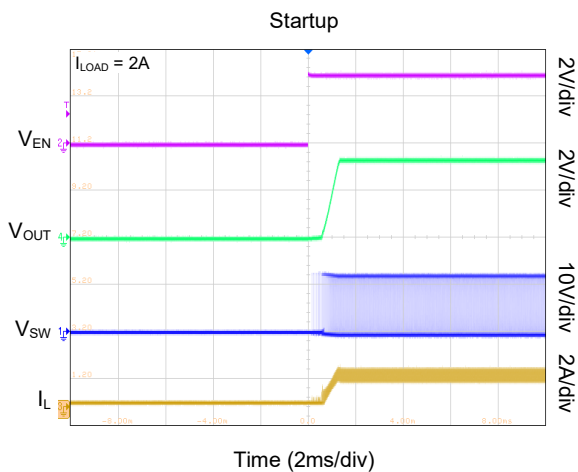
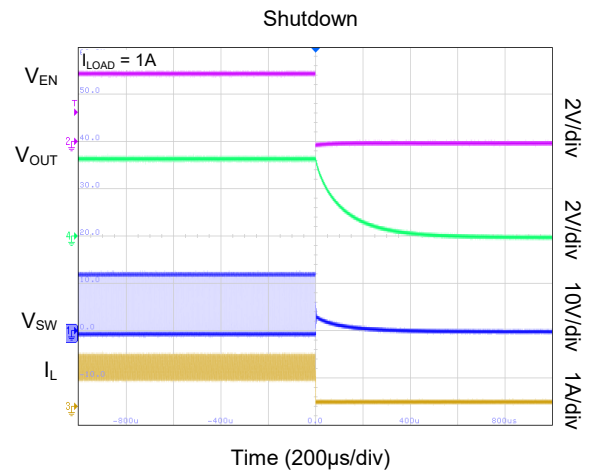
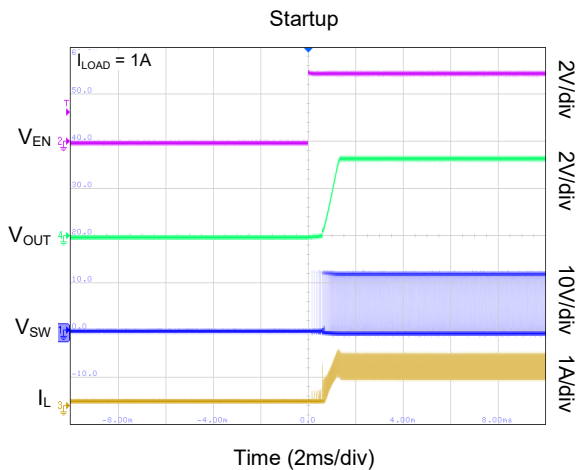
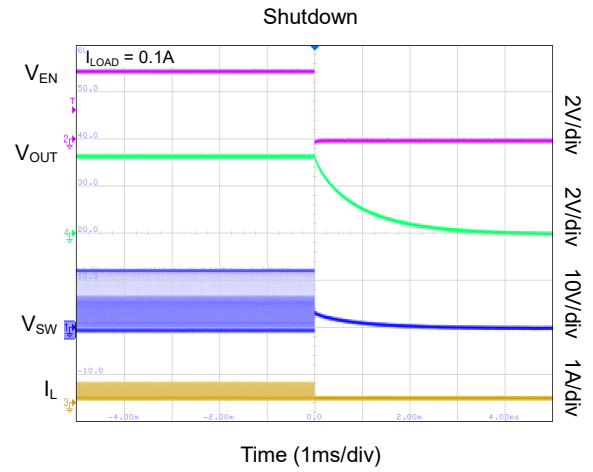
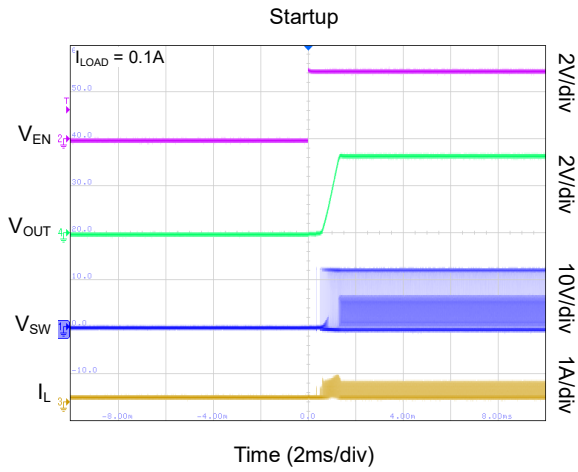
(V_{IN} = 12V, V_{EN} = 2V, T_J = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Feedback Voltage	V _{FB}	V _{IN} = 12V	0.792	0.803	0.814	V
		T _J = -40°C to +125°C	0.783		0.820	
Switch On-Resistance	R _{DSON}	V _{BOOT} - V _{SW} = 5V		220	270	mΩ
		T _J = -40°C to +125°C			430	
Switch Leakage Current	I _{LKG}	V _{EN} = 0V, V _{SW} = 0V		1		μA
Current Limit	I _{LIM}		3.08	3.79	4.38	A
COMP to Sensed Current Transconductance	G _{CS}			5.85		A/V
Error Amplifier Voltage Gain ⁽¹⁾	A _{EA}			80		dB
Error Amplifier Transconductance	G _{EA}	I _{COMP} = ±3μA		120		μA/V
Error Amplifier Source Current	I _{SOURCE}	V _{FB} = 0.7V, V _{COMP} = 1V		9		μA
Error Amplifier Sink Current	I _{SINK}	V _{FB} = 0.9V, V _{COMP} = 1V		-9		μA
VIN Under-Voltage Lockout Threshold (UVLO)	V _{UVLO}		2.87	3.16	3.48	V
		T _J = -40°C to +125°C	2.70		3.70	
VIN Under-Voltage Lockout Hysteresis	V _{UVLOHYS}			0.61		V
Soft-Start Time ⁽¹⁾	t _{SS}	From 10% to 90% × V _{OUT} (set)		0.55		ms
Switching Frequency	f _{SW}	R ₄ = 89kΩ	0.900	0.985	1.100	MHz
		R ₄ = 89kΩ, T _J = -40°C to +125°C	0.890		1.105	
Shutdown Supply Current	I _{SD}	V _{IN} = 12V, V _{EN} < 0.2V		13	18	μA
Quiescent Supply Current	I _Q	No load, V _{FB} = 0.86V		126		μA
Thermal Shutdown Temperature	T _{SD}			155		°C
Thermal Shutdown Temperature Hysteresis	T _{HYS}			20		°C
Minimum Off Time ⁽¹⁾	t _{OFF_MIN}			100		ns
Minimum On Time ⁽¹⁾	t _{ON_MIN}			100		ns
EN Rising Threshold	V _{ENR}		1.40	1.58	1.75	V
		T _J = -40°C to +125°C	1.35		1.85	
EN Threshold Hysteresis	V _{ENHYS}			460		mV

NOTE: 1. Guaranteed by design.

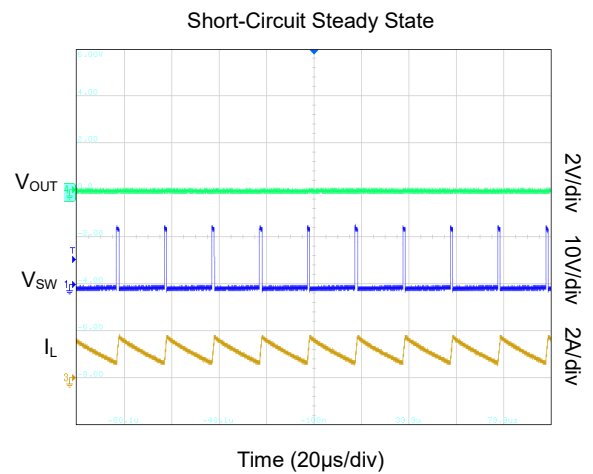
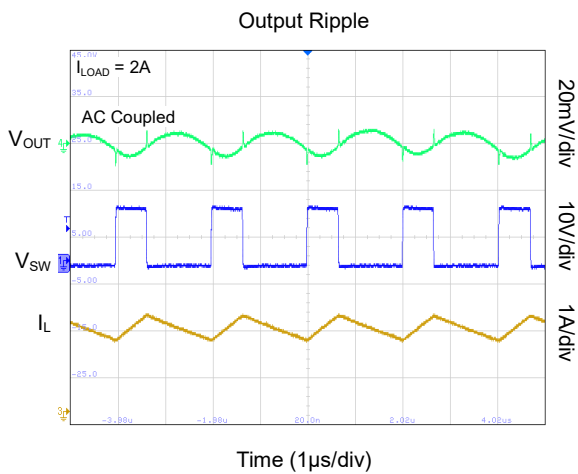
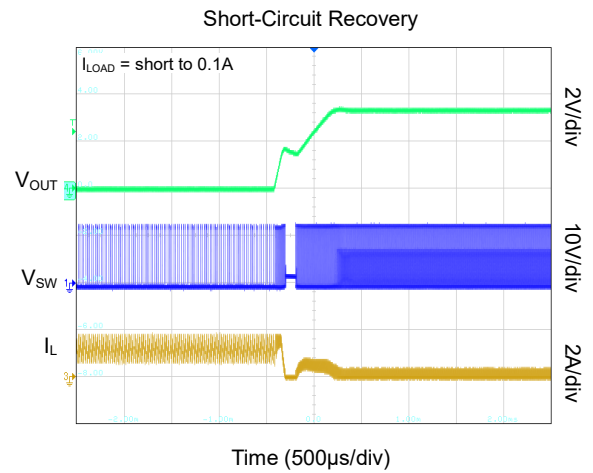
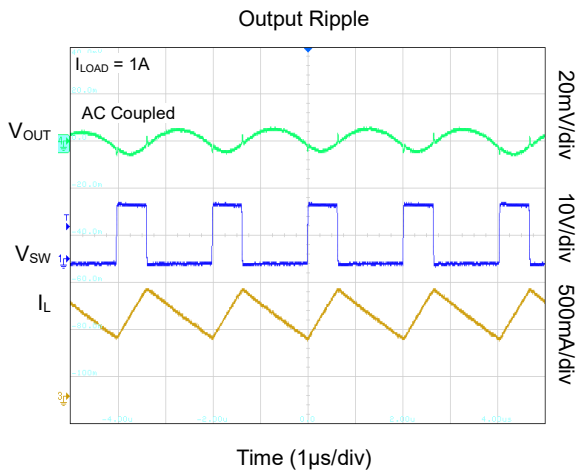
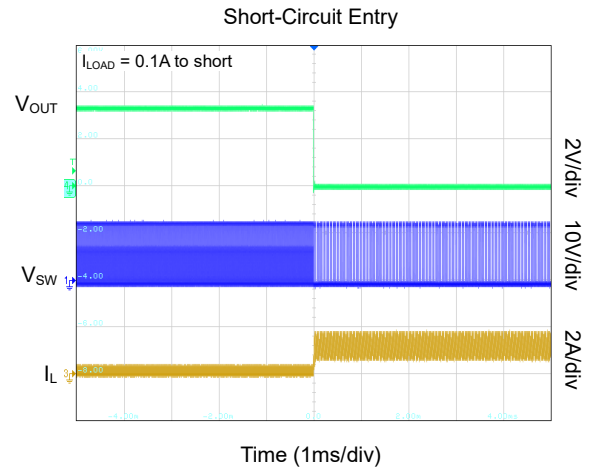
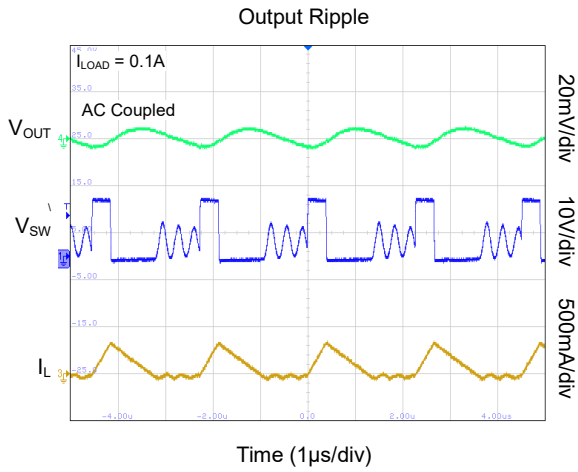
TYPICAL PERFORMANCE CHARACTERISTICS

V_{IN} = 12V, V_{OUT} = 3.3V, C_{IN} = 10μF, C_{OUT} = 22μF, L₁ = 10μH, DCR = 15.3mΩ, unless otherwise noted.



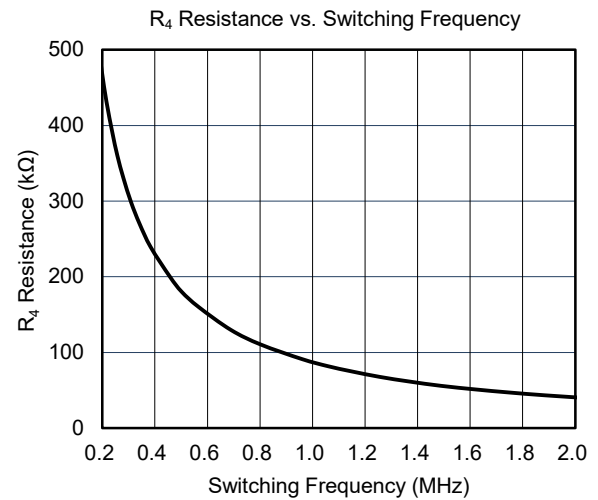
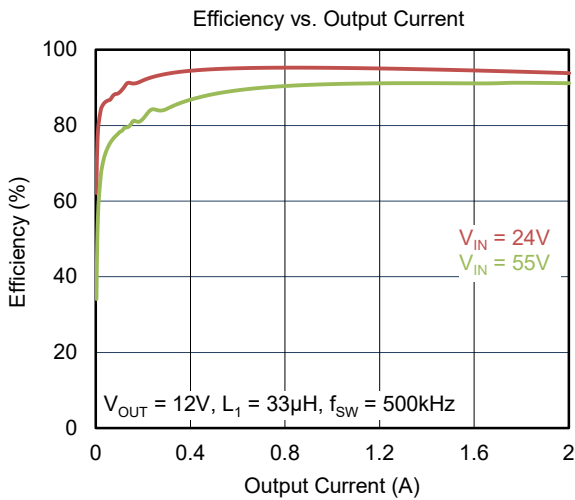
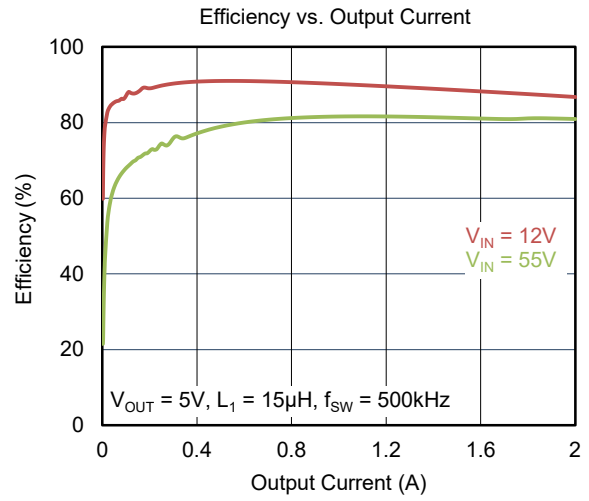
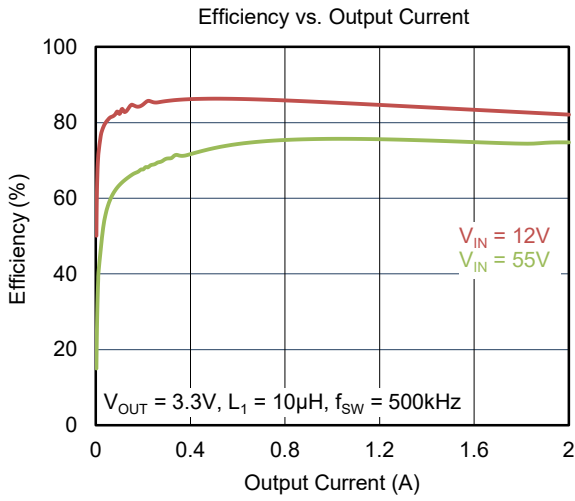
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.3V$, $C_{IN} = 10\mu F$, $C_{OUT} = 22\mu F$, $L_1 = 10\mu H$, $DCR = 15.3m\Omega$, unless otherwise noted.



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.3V$, $C_{IN} = 10\mu F$, $C_{OUT} = 22\mu F$, $L_1 = 10\mu H$, $DCR = 15.3m\Omega$, unless otherwise noted.



FUNCTIONAL BLOCK DIAGRAM

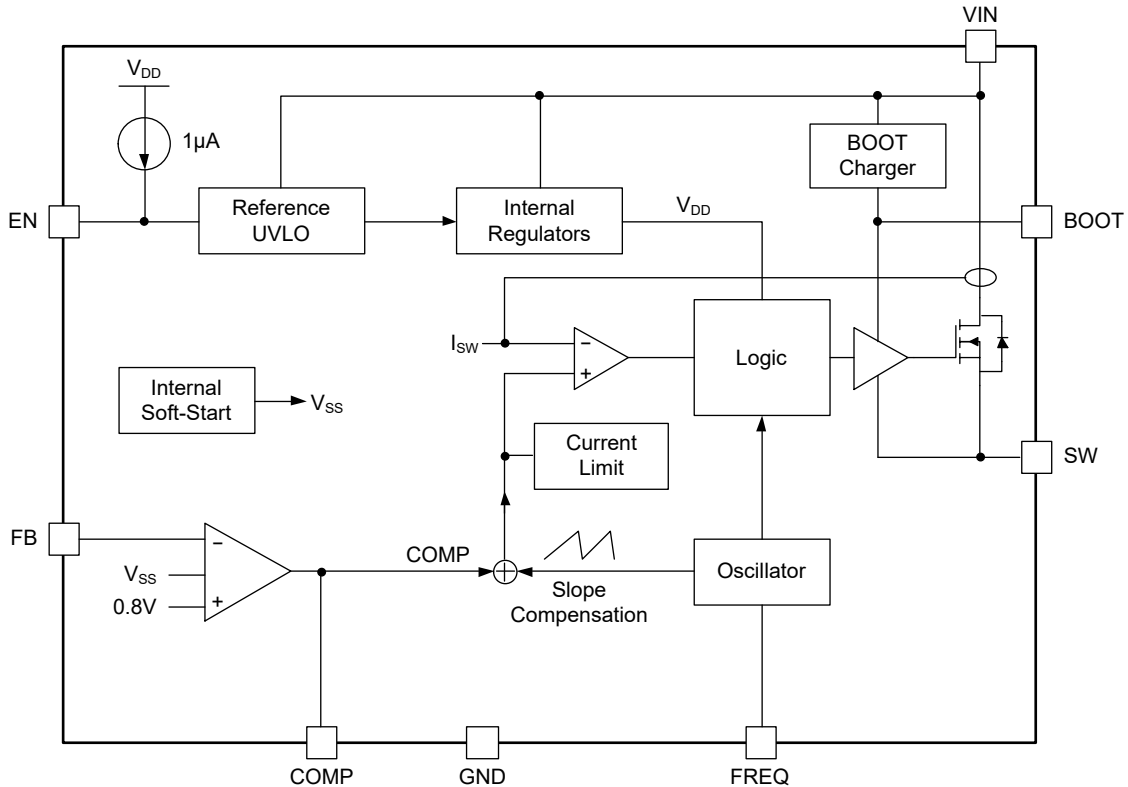


Figure 2. SGM6060 Functional Block Diagram

DETAILED DESCRIPTION

Overview

The SGM6060 is a 3.8V to 55V, 2A non-synchronous Buck converter with integrated high-side N-channel MOSFET. It is a perfect solution for efficient single stage Buck applications. The integrated functions include precision current limiting, automatically switched PWM and PFM modes, soft-start circuit and wide range switching frequency, which can meet different requirements. Peak current mode control is implemented to provide fast load transient response and simple compensation.

VIN Under-Voltage Lockout (UVLO)

The SGM6060 integrates VIN under-voltage lockout (UVLO) feature to protect the device from malfunctioning when the input voltage is insufficient to properly power up the internal circuits. The UVLO rising threshold is 3.16V (TYP) and has a 0.61V (TYP) hysteresis.

Internal 2.8V Regulator

An internal 2.8V regulator powers most of the device internal circuits. The 2.8V output is fully regulated when VIN exceeds 3.16V. It will drop if VIN falls below 3.16V.

Enable Input

The EN pin is an active high input to enable or disable the device. The EN rising threshold voltage VENR is 1.58V (TYP) and has a 460mV (TYP) hysteresis.

A 1µA internal current source pulls the EN pin up to approximately 3.0V. Therefore the device will be enabled when the EN pin is left floating. To disable the device, pull the EN pin down below 1.12V with at least 1µA sink capability.

When VEN falls below 1.12V, the device is disabled and enters low shutdown current mode. When VEN exceeds 0V and does not reach VENR, the device is still disabled but with slightly higher shutdown current.

DETAILED DESCRIPTION

Startup and Shutdown

If both V_{IN} and V_{EN} exceed their thresholds, the device is enabled and starts operation. First, the bandgap circuit starts working to generate stable reference voltage and bias current. Then two internal regulators are established to provide supply voltage for internal analog and digital circuit respectively. About 30 μ s later, bootstrap capacitor voltage is charged above UVLO threshold. Then the output starts to rise slowly during soft-start.

The device is disabled when any of invalid EN voltage, VIN UVLO and thermal shutdown events occurs. Once the device is disabled, the high-side switch is turned off immediately to avoid any other fault triggering.

Soft-Start and Ramp

Every time the device is enabled (after power-up, pulling EN high), the output voltage is gradually increased to its regulation value with a ramp (after a brief 50 μ s hold). Soft-start is needed to prevent triggering of current limit or short-circuit protections or to avoid output overshooting during startup. Without a soft-start, the inrush currents of the output capacitors or the load can cause over-current and the protection procedure results in non-monotonic startup or even instability. Overshooting may also occur during startup after short-circuit recovery. The internal soft-start voltage (V_{SS}) and reference (V_{REF}) are both sent to the error amplifier and the lower value of them is the actual reference that is compared with the feedback voltage (V_{FB}).

PWM Operation Mode

In the moderate to heavy load conditions, the SGM6060 runs at fixed frequency with peak current control mode. The high-side MOSFET is turned on at the leading edge of internal clock until the sensing current ramp signal reaches the COMP voltage. If the switch current does not reach the reference value (conversion from V_C) in a cycle, the switch will also be turned off for t_{OFF_MIN} (100ns, TYP) before the next clock.

PFM Mode

In the light load condition, the frequency is reduced depending on the load to minimize the switching and gate driving losses and keep the efficiency high.

PWM Comparator and Current Limit

For peak current mode, a signal represent of high-side current is used as the input of PWM comparator, which is accurately sampled by internal sensing circuit. After 100ns typical blanking time, the signal is compared with COMP to determine switching state of high-side MOSFET. The cycle-by-cycle current limit threshold is approximately 3.79A.

Note that the measured peak current limits in the closed-loop and open-loop test conditions are slightly different, mainly caused by the propagation delay.

Short-Circuit Protection and Recovery

If the output is shorted to the ground, the switching frequency is reduced. The foldback current limit is reduced by half to lower the power consumption. During output shorted condition, V_{SS} is pulled down to about 0.1V above V_{FB} to reduce the overshoot of short recovery. The current limit resumes its normal value when V_{FB} exceeds 0.4V.

Bootstrap Floating MOSFET Driver

The power of the high-side MOSFET driver is provided by an external capacitor between BOOT and SW pins. An internal bootstrap regulator keeps the bootstrap capacitor charged and regulated to approximately 4.5V.

The bootstrap voltage is detected by internal BOOT UVLO circuit with 2.4V rising threshold and 250mV hysteresis. If the bootstrap voltage falls below its UVLO threshold, the power MOSFET is turned off immediately. An internal transistor is used to pull down the SW node to make sure BOOT capacitor is charged sufficiently. This design can obviously reduce the output voltage ripple at small input/output voltage difference and no load. When the bootstrap voltage is charged above threshold, the pull-down transistor is turned off and high-side MOSFET is able to be turned on again.

Except for BOOT UVLO condition, the external circuit connected to the SW serves as the return path to GND for the charge current. Enough voltage headroom should be left to facilitate the charging. When the external freewheeling diode is on, bootstrap charging starts until the regulated voltage.

DETAILED DESCRIPTION (continued)

The converter operates in PFM Mode at no load or light load, to minimize switching losses and keep the output regulated. In this mode, the available time for refreshing the BOOT voltage is reduced, bootstrap voltage will drop below the regulated voltage (4.5V). The maximum charged voltage is equal to $V_{IN} - V_{OUT}$. If the difference of $V_{IN} - V_{OUT}$ is too small, BOOT UVLO can be triggered. The internal charging circuit charges the bootstrap capacitor by the set frequency, until BOOT UVLO is released.

The designer should make sure that the SW node bleeding current is higher than the quiescent current of the floating driver (approximately $20\mu\text{A}$). Usually the feedback resistors (R_1 and R_2) are selected such that the $R_1 + R_2$ value is small enough to provide that current:

$$I_{OUT_MIN} + \frac{V_{OUT}}{(R_1 + R_2)} > 20\mu\text{A} \quad (1)$$

External Bootstrap Diode

To improve the efficiency, using an external boot diode supplied from a 5V rail (in Figure 3) is recommended in the following cases:

- A 5V rail is available.
- V_{IN} is less than 5V.
- V_{OUT} is between 3.3V and 5V.
- High duty cycle applications ($V_{OUT}/V_{IN} > 65\%$).

A low-cost diode like IN4148 or BAT54 can be used.

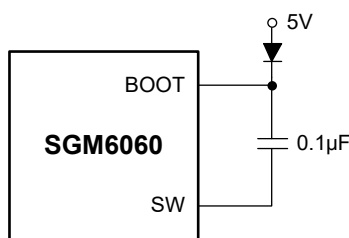


Figure 3. External Bootstrap Diode

Adjustable Switching Frequency

The switching frequency is adjusted by connecting an external resistor (R_4) between the FREQ and GND. Use Equation 2 to calculate R_4 resistance:

$$R_4(\text{k}\Omega) = \frac{94581}{f_{sw}(\text{kHz})} - 7.24 \quad (2)$$

For Example, to get 500kHz switching frequency, the required R_4 resistor is 180k Ω .

An internal frequency foldback technique is designed by monitoring the FB voltage. It can effectively avoid the inductor current runaway during startup or restarting in certain situation.

Error Amplifier (EA)

The output voltage is sensed by a resistor divider through the FB pin and is compared with the internal reference. The EA generates an output current that is proportional to the voltage difference (error). This current is fed into the external compensation network to generate the V_C voltage on the COMP pin, which sets the reference value for the peak current that controls the on time of the power MOSFET.

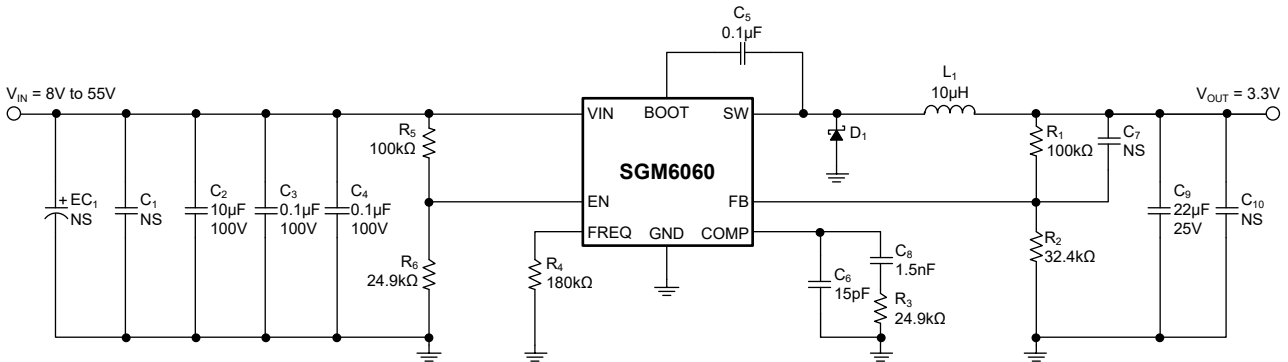
The operating voltage range of COMP (V_C) is between 0.75V and 2.0V in normal conditions. COMP is pulled down to the ground when the device shuts down. The COMP voltage must not be pulled higher than 2.8V.

Thermal Shutdown

To protect the device from damage due to overheating, a thermal shutdown feature is implemented to disable the device when the die temperature exceeds $+155^\circ\text{C}$ (TYP). The chip is automatically enabled when the temperature falls below $+135^\circ\text{C}$ (20°C hysteresis, TYP).

APPLICATION INFORMATION

In this section, power supply design with the SGM6060 non-synchronous Buck converter and selection of the external component will be explained based on the typical application that is applicable for various input and output voltage combinations.



NOTE: EC₁ and C₁ are optional. If the input voltage is far away from the VIN of SGM6060, EC₁ and C₁ should be installed.

Figure 4. SGM6060 Application Example with 3.3V/2A Output

Design Requirements

In this example, a high frequency regulator with ceramic output capacitors will be designed using SGM6060 and the details will be reviewed. The design requirements are typically determined at the system level. The known requirements are summarized in Table 1.

Table 1. Design Parameters

Design Parameter	Example Value
Output Voltage	3.3V
Maximum Output Current	2A
Load Transient Response of 1A - 2A Step	$\Delta V_{OUT} = 7\%$
Input Voltage Range	12V nominal, 8V to 55V
Maximum Output Voltage Ripple	33mV _{P-P}
Turn-On Input Voltage (Rising V _{IN})	7.9V
Turn-Off Input Voltage (Falling V _{IN})	5.6V
Switching Frequency (f _{SW})	500kHz

Operating Frequency

Usually the first parameter to design is the switching frequency (f_{SW}). Higher switching frequencies allow smaller solution size and smaller filter inductors and capacitors, and the bandwidth of the converter can be increased for faster response. It is also easier to filter noises because they also shift to higher frequencies. The drawbacks are increased switching and gate driving losses that result in lower efficiency and tighter thermal limits. Also the duty cycle range and step-down ratio will be limited due to the minimum on time and/or

off time limits of the converter. In this design, f_{SW} = 500kHz is chosen as a tradeoff. From Equation 2, the nearest standard resistor for this frequency is R₄ = 180kΩ.

Inductor Design

Equation 3 is conventionally used to calculate the output inductance of a Buck converter. Generally, a smaller inductor is preferred to allow larger bandwidth and smaller size. The ratio of inductor current ripple (ΔI_L) to the maximum output current (I_{OUT}) is represented as K_{IND} factor (ΔI_L/I_{OUT}). The inductor ripple current is bypassed and filtered by the output capacitor and the inductor DC current is passed to the output. Inductor ripple is selected based on a few considerations. The peak inductor current (I_{OUT} + ΔI_L/2) must have a safe margin from the saturation current of the inductor in the worst-case conditions especially if a hard-saturation core type inductor (such as ferrite) is chosen. During power-up with large output capacitor, over-current, output shorted or load transient conditions, the actual peak current of inductor can be greater than I_{LPEAK} calculated in Equation 6. For peak current mode converter, selecting an inductor with saturation current above the switch current limit is sufficient. Typically, a 20% to 40% ripple is selected (K_{IND} = 0.2 ~ 0.4). Choosing a higher K_{IND} value reduces the selected inductance.

$$L_1 = \frac{V_{INMAX} - V_{OUT}}{I_{OUT} \times K_{IND}} \times \frac{V_{OUT}}{V_{INMAX} \times f_{SW}} \quad (3)$$

APPLICATION INFORMATION (continued)

In this example, $K_{IND} = 0.3$ is chosen and the inductance is calculated to be $10.34\mu\text{H}$. In this example, the nearest standard value $10\mu\text{H}$ is selected. The ripple, RMS and peak inductors current calculations are summarized in Equations 4, 5 and 6 respectively.

$$\Delta I_L = \frac{V_{INMAX} - V_{OUT}}{L_1} \times \frac{V_{OUT}}{V_{INMAX} \times f_{SW}} \quad (4)$$

$$I_{LRMS} = \sqrt{I_{OUT}^2 + \frac{\Delta I_L^2}{12}} \quad (5)$$

$$I_{LPEAK} = I_{OUT} + \frac{\Delta I_L}{2} \quad (6)$$

The ripple, RMS, and peak inductor currents are calculated as 0.62A , 2.01A and 2.31A respectively. A $10\mu\text{H}$ inductor from Sunlord SWPA8040S100MT with 4.1A saturation and 3.3A RMS current ratings is selected.

External Diode (D)

The SGM6060 adopts non-synchronous architecture. Therefore an external diode is required to place between SW and GND pins. A Schottky diode is recommended due to the characteristics of fast recovery and small forward conduction voltage drop, which can help improve the efficiency and reduce the rising edge ring of SW node.

For main parameters of diode, the maximum reverse voltage rating of the selected diode must be greater than the maximum applicable input voltage. The peak current rating must be greater than the current limit, and the average forward current should be greater than typical load current with enough margin.

In this example, a B380-13-F from Diodes Inc. with 80V reverse voltage and 3A forward current is selected.

Output Capacitor Design

Three primary criteria must be considered for design of the output capacitor (C_{OUT}): (1) the converter pole location, (2) the output voltage ripple, (3) the transient response to a large change in load current. The selected value must satisfy all of them. The desired transient response is usually expressed as maximum overshoot, maximum undershoot, or maximum recovery time of V_{OUT} in response to a large load step. Transient response is usually the more stringent criteria in low output voltage applications. The output capacitor must provide the increased load current or absorb the excess inductor current (when the load current steps down) until the control loop can re-adjust the current of the inductor to the new load level. Typically, it requires

two or more cycles for the loop to detect the output change and respond (change the duty cycle). It may also be expressed as the maximum output voltage drop or rise when the full load is connected or disconnected (100% load step). Equation 7 can be used to calculate the minimum output capacitance that is needed to supply or absorb a current step (ΔI_{OUT}) for at least 2 cycles until the control loop responds to the load change with a maximum allowed output transient of ΔV_{OUT} (overshoot or undershoot).

$$C_{OUT} > \frac{2 \times \Delta I_{OUT}}{f_{SW} \times \Delta V_{OUT}} \quad (7)$$

For example, if the acceptable transient to a 1A load step is 7% , by inserting $\Delta V_{OUT} = 0.07 \times 3.3\text{V} = 0.231\text{V}$ and $\Delta I_{OUT} = 1\text{A}$, the minimum required capacitance will be $17.3\mu\text{F}$. Generally, the ESR of ceramic capacitors is small enough. The impact of output capacitor ESR on the transient is not taken into account in Equation 7.

Equation 8 can be used for the output ripple criteria and finding the minimum output capacitance needed. $V_{ORIPPLE}$ is the maximum acceptable ripple. In this example, the allowed ripple is 33mV that results in minimum capacitance of $4.7\mu\text{F}$.

$$C_{OUT} > \frac{1}{8 \times f_{SW}} \times \frac{\Delta I_L}{V_{ORIPPLE}} \quad (8)$$

Note that the impact of output capacitor ESR on the ripple is not considered in Equation 8. Use Equation 9 to calculate the maximum acceptable ESR of the output capacitor to meet the output voltage ripple requirement. In this example, the ESR must be less than $33\text{mV}/0.62\text{A} = 53.2\text{m}\Omega$.

$$R_{ESR} < \frac{V_{ORIPPLE}}{\Delta I_L} \quad (9)$$

Higher nominal capacitance value must be chosen due to aging, temperature, and DC bias derating of the output capacitors. In this example, a $22\mu\text{F}/25\text{V}$ ceramic capacitor with X7R dielectric and $3\text{m}\Omega$ ESR is selected. There is a limit to the amount of ripple current that a capacitor can handle without damage or overheating. The inductor ripple is bypassed through the output capacitor. Equation 10 calculates the RMS current that the output capacitor must support. In this example, it is 179mA .

$$I_{CORMS} = \frac{\Delta I_L}{\sqrt{12}} \quad (10)$$

APPLICATION INFORMATION (continued)

Input Capacitor Design

A high-quality ceramic capacitor (X5R or X7R or better dielectric grade) must be used for input decoupling of the SGM6060. If input power is far away from SGM6060, additional bulk capacitor is recommended in parallel to stabilize input voltage. The RMS value of input capacitor can be calculated from Equation 11 and the maximum I_{CIRMS} occurs at 50% duty cycle. For this example, the maximum input RMS current is 1A. The ripple current rating of input capacitor should be greater than I_{CIRMS} .

$$I_{CIRMS} = I_{OUTMAX} \times \sqrt{D \times (1-D)} \quad (11)$$

where D is the duty cycle.

In this example, the voltage rating of capacitor should have a safe margin from maximum input voltage. Therefore, a 10 μ F/100V ceramic capacitor is selected for V_{IN} to cover all DC bias, thermal and aging deratings, and two 0.1 μ F/100V capacitors are selected for further decoupling of high frequency noise. The small capacitors should be connected between V_{IN} and GND pins as close as possible.

The input voltage ripple can be calculated from Equation 12, and the maximum ripple occurs at 50% duty cycle.

$$\Delta V_{IN} = \frac{I_{OUTMAX} \times D \times (1-D)}{C_{IN} \times f_{SW}} \quad (12)$$

Bootstrap Capacitor Selection

A 0.1 μ F ceramic capacitor with 10V or higher voltage rating must be connected between the BOOT and SW pin. X5R or better dielectric types are recommended.

UVLO Setting

The under-voltage lockout (UVLO) can be programmed by an external voltage divider network. In this design, the turn-on (enable to start switching) occurs when V_{IN} rises above 7.9V ($V_{STARTUP}$). When the regulator is in operation, it will not stop switching (disabled) until the input falls below 5.6V ($V_{SHUTDOWN}$). Use Equation 13 to calculate the resistors value. In this example, choose $R_5 = 100k\Omega$ and $R_6 = 24.9k\Omega$.

$$R_5 = R_6 \times \frac{V_{STARTUP} - V_{ENR}}{V_{ENR}} \quad (13)$$

Feedback Resistors

Choosing a 100k Ω value for the upper resistor (R_1), the lower resistor (R_2) can be calculated from Equation 14. The nearest 1% resistor for the calculated value (32k Ω) is 32.4k Ω . For higher output accuracy, choose resistors with better tolerance (0.5% or better).

$$R_2 = \frac{V_{REF}}{V_{OUT} - V_{REF}} \times R_1 \quad (14)$$

Loop Compensation Design

Several techniques are used by engineers to compensate a DC/DC regulator. In this simplified method, the effects of the slope compensation are ignored. Because of this approximation, the actual cross over frequency is usually lower than the calculated value.

First, the converter pole (f_p), and ESR zero (f_z) are calculated from Equations 15 and 16. For C_{OUT} , the worst derated value of 17 μ F should be used. Equations 17 and 18 can be used to find an estimation for closed-loop crossover frequency (f_{CO}) as a starting point (choose the lower value).

$$f_p = \frac{I_{OUT}}{2\pi \times V_{OUT} \times C_{OUT}} \quad (15)$$

$$f_z = \frac{1}{2\pi \times R_{ESR} \times C_{OUT}} \quad (16)$$

$$f_{CO} = \sqrt{f_p \times f_z} \quad (17)$$

$$f_{CO} = \sqrt{f_p \times \frac{f_{SW}}{2}} \quad (18)$$

For this design, $f_p = 5.68kHz$ and $f_z = 3.12MHz$. Equation 17 yields 133.1kHz for crossover frequency and Equation 18 gives 37.7kHz. As the influence of slope compensation in the actual circuit, a slightly higher frequency of 40kHz is selected.

APPLICATION INFORMATION (continued)

Having the crossover frequency, the compensation network (R_3 and C_8) can be calculated. R_3 sets the gain of the compensated network at the crossover frequency and can be calculated by Equation 19.

$$R_3 = \frac{2\pi \times f_{CO} \times V_{OUT} \times C_{OUT}}{G_{EA} \times V_{REF} \times G_{CS}} \quad (19)$$

C_8 sets the location of the compensation zero along with R_3 . To place this zero on the converter pole, use Equation 20.

$$C_8 = \frac{V_{OUT} \times C_{OUT}}{I_{OUT} \times R_3} \quad (20)$$

From Equations 19 and 20, the standard selected values are $R_3 = 24.9k\Omega$ and $C_8 = 1.5nF$.

A high frequency pole can also be added by a parallel capacitor if needed (not used in this example). The pole frequency can be calculated from Equation 21.

$$f_p = \frac{1}{2\pi \times R_3 \times C_6} \quad (21)$$

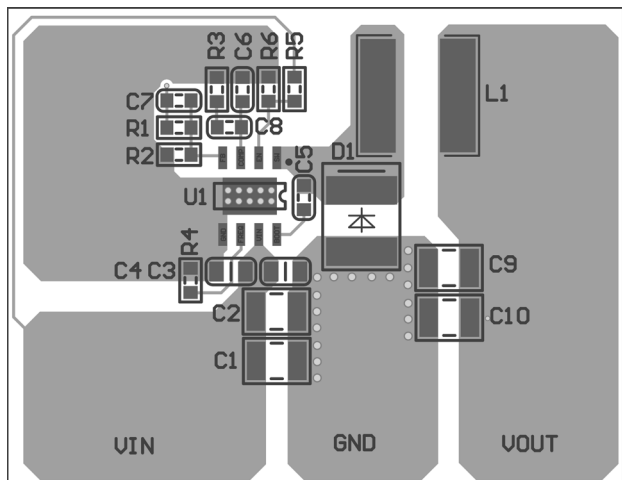
Layout Considerations

PCB layout is critical for stable and high-performance converter operation. The recommend layout is shown in Figure 5.

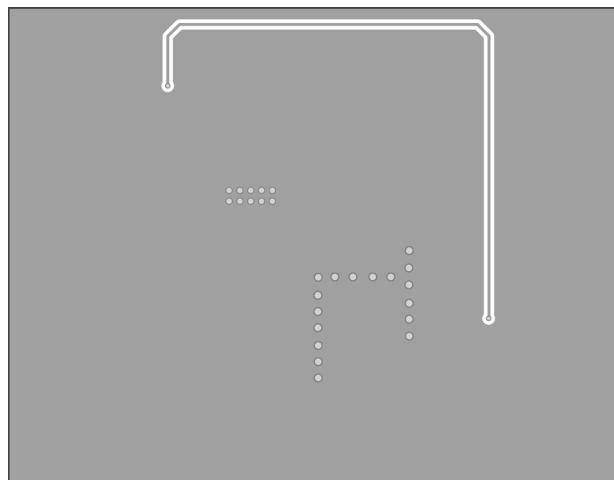
- Place the nearest input high frequency decoupling capacitor (0.1 μ F) between VIN and GND pins as close as possible.

- Place the larger input ceramic capacitor and Schottky diode close to relevant pins for minimizing the influence of ground bounce.
- Use short and wide trace to connect SW node to the inductor. Minimize the area of switching loop. Otherwise, large voltage spikes on the SW node and poor EMI performance are inevitable.
- Sensitive signal like FB, COMP, EN traces must be placed away from high dv/dt nodes (such as SW) and not inside any high di/dt loop (like capacitor or switch loops). The ground of these signals should be connected to GND pin and separated with power ground.
- To improve the thermal relief, use a group of thermal vias under the exposed pad to transfer the heat to the ground planes in the opposite side of the PCB. Use small vias (approximately 15mil) such that they can be filled up during the reflow soldering process to provide a good metallic heat conduction path from the IC exposed pad to the other PCB side.
- Connect VIN, GND and exposed pad pins to large copper areas to increase heat dissipation and long-term reliability. Keep SW area small to avoid emission issue.

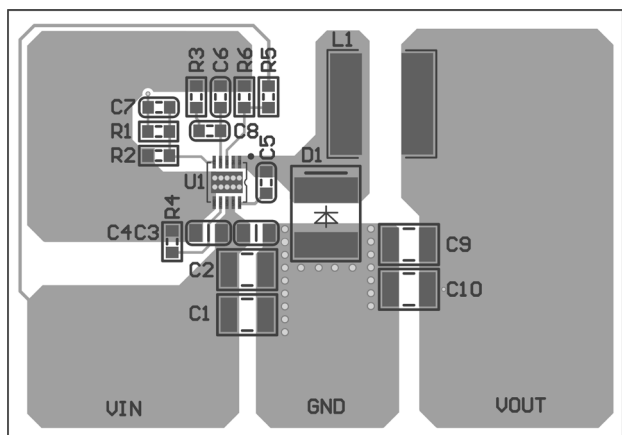
APPLICATION INFORMATION (continued)



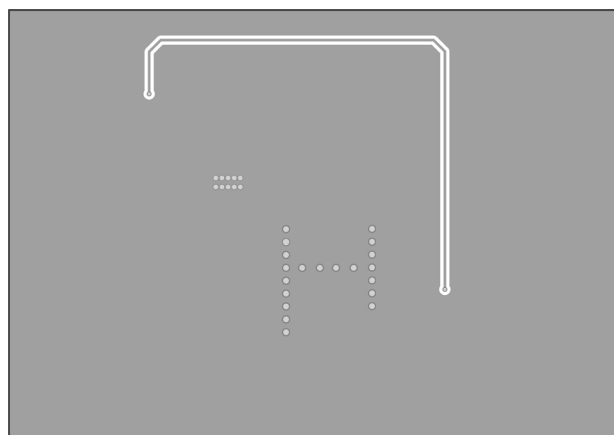
TDFN-3x3-10L Top Layer



TDFN-3x3-10L Bottom Layer



SOIC-8 (Exposed Pad) Top Layer



SOIC-8 (Exposed Pad) Bottom Layer

Figure 5. PCB Layout Guide

ADDITIONAL TYPICAL APPLICATION CIRCUITS

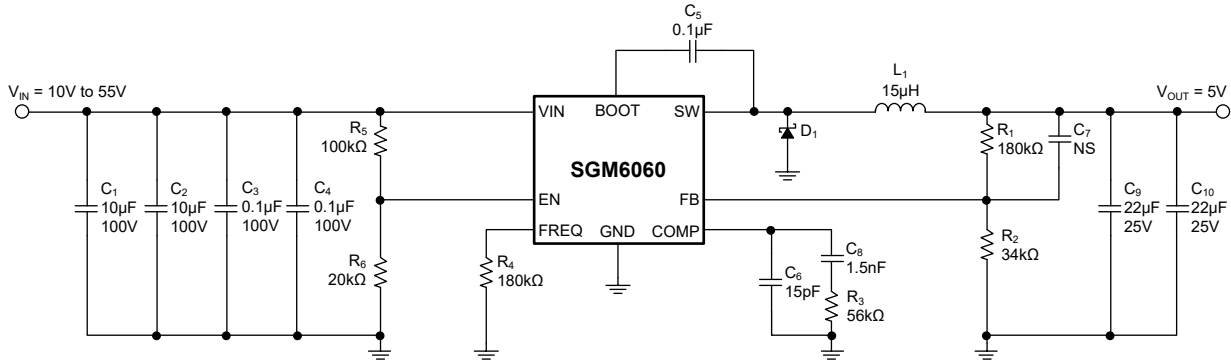


Figure 6. 5V Output Typical Application (NS: not soldered)

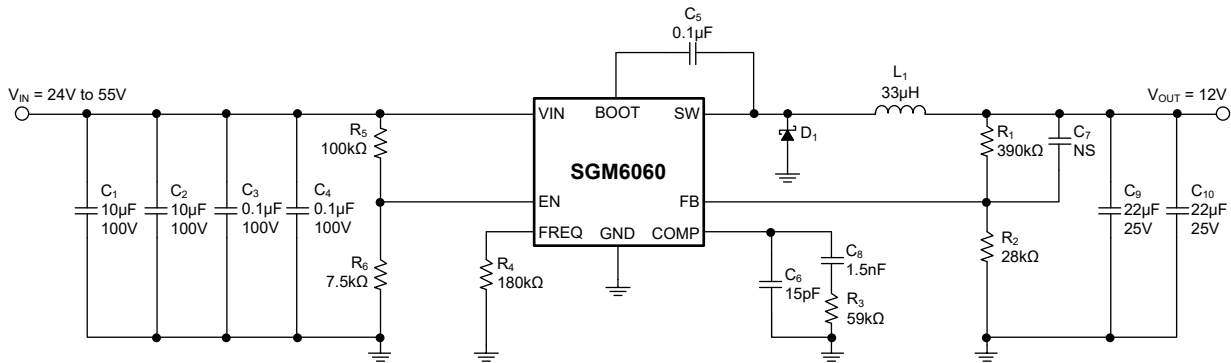


Figure 7. 12V Output Typical Application (NS: not soldered)

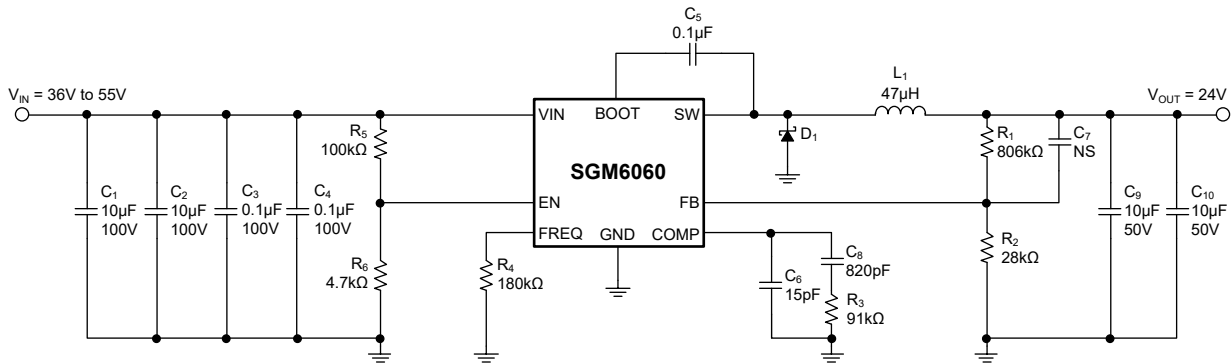


Figure 8. 24V Output Typical Application (NS: not soldered)

REVISION HISTORY

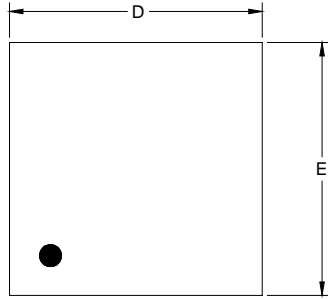
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Original (DECEMBER 2022) to REV.A

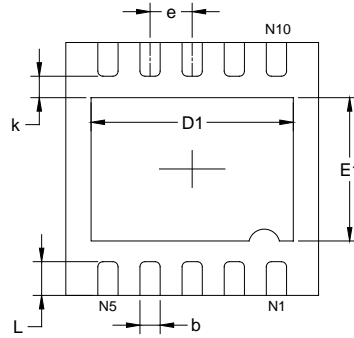
Changes from Original (DECEMBER 2022) to REV.A	Page
Changed from product preview to production data.....	All

PACKAGE OUTLINE DIMENSIONS

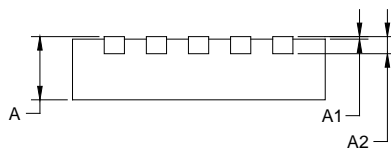
TDFN-3x3-10L



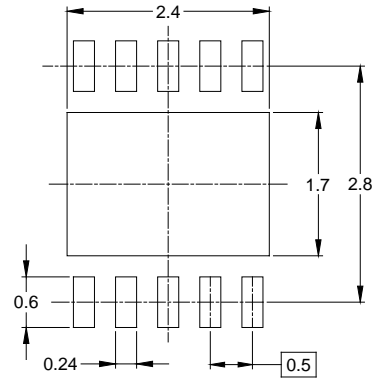
TOP VIEW



BOTTOM VIEW



SIDE VIEW



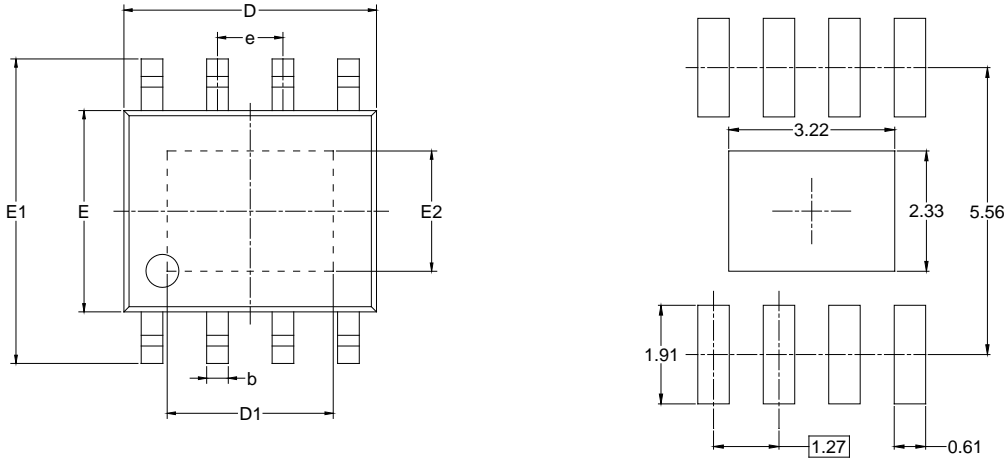
RECOMMENDED LAND PATTERN (Unit: mm)

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A2	0.203 REF		0.008 REF	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.103
E	2.900	3.100	0.114	0.122
E1	1.500	1.800	0.059	0.071
k	0.200 MIN		0.008 MIN	
b	0.180	0.300	0.007	0.012
e	0.500 TYP		0.020 TYP	
L	0.300	0.500	0.012	0.020

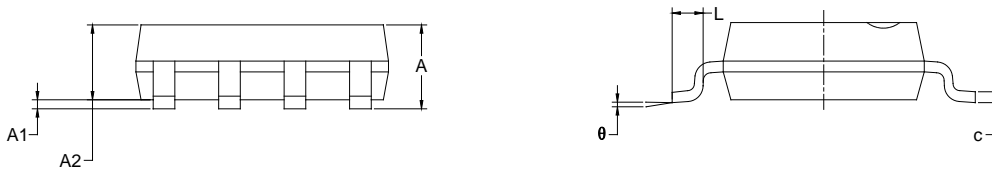
NOTE: This drawing is subject to change without notice.

PACKAGE OUTLINE DIMENSIONS

SOIC-8 (Exposed Pad)



RECOMMENDED LAND PATTERN (Unit: mm)



Symbol	Dimensions In Millimeters		
	MIN	MOD	MAX
A			1.700
A1	0.000	-	0.150
A2	1.250	-	1.650
b	0.330	-	0.510
c	0.170	-	0.250
D	4.700	-	5.100
D1	3.020	-	3.420
E	3.800	-	4.000
E1	5.800	-	6.200
E2	2.130	-	2.530
e	1.27 BSC		
L	0.400	-	1.270
θ	0°	-	8°

NOTES:

1. Body dimensions do not include mode flash or protrusion.
2. This drawing is subject to change without notice.

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
TDFN-3×3-10L	13"	12.4	3.35	3.35	1.13	4.0	8.0	2.0	12.0	Q1
SOIC-8 (Exposed Pad)	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1

D00001

PACKAGE INFORMATION

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
13"	386	280	370	5

DD0002